ETCHING METHOD AND PLASMA PROCESSING SYSTEM

Abstract

An etching method including: (a) preparing a substrate on a substrate support, the substrate including an underlying film, an etching target film on the underlying film, the etching target film including at least one selected from the group consisting of silicon, germanium, and a metal, and a mask on the etching target film, the mask including at least one opening that exposes the etching target film; (b) etching the etching target film with plasma generated from a first processing gas including Cl_2 gas; and (c) further etching the etching target film with plasma generated from a second processing gas including HCl gas.

Fig. 3